imall

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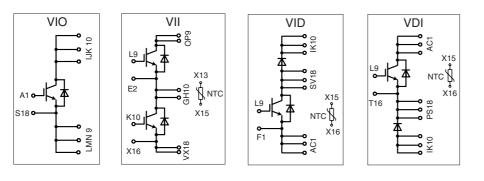




IGBT Modules in ECO-PAC 2

Short Circuit SOA Capability Square RBSOA

Preliminary data sheet



IGBTs

Symbol	Conditions	Maximum	Ratings
V _{CES}	$T_{VJ} = 25^{\circ}C$ to $150^{\circ}C$	600	V
V _{GES}		± 20	V
I _{C25} I _{C80}	$T_{c} = 25^{\circ}C$ $T_{c} = 80^{\circ}C$	121 83	A
I _{CM} V _{CEK} ∫	$V_{GE} = \pm 15 \text{ V}; \text{ R}_{G} = 2.2 \Omega; \text{ T}_{VJ} = 125^{\circ}\text{C}$ RBSOA, Clamped inductive load; L = 100 µH	200 360	AV
t _{sc} (SCSOA)	$V_{CE} = V_{CES}$; $V_{GE} = \pm 15$ V; $R_{G} = 2.2 \Omega$; $T_{VJ} = 125^{\circ}C$ non-repetitive	10	μs
P _{tot}	$T_c = 25^{\circ}C$	379	W

Symbol Conditions

Symbol	Conditions $(T_{VJ} = 25^{\circ}C)$		aracteria otherwis		
		min.	typ.	max.	
V _{CE(sat)}	$I_{c} = 130 \text{ A}; V_{GE} = 15 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		2.3 2.6	2.9	V V
V _{GE(th)}	$I_{c} = 1.5 \text{ mA; } V_{GE} = V_{CE}$	4.5		6.5	V
I _{CES}	$V_{_{CE}} = V_{_{CES}};$ $V_{_{GE}} = 0 V;$ $T_{_{VJ}} = 25^{\circ}C$ $T_{_{VJ}} = 125^{\circ}C$			1.2 7.5	mA mA
I _{GES}	$V_{ce} = 0 \text{ V}; \text{ V}_{ge} = \pm 20 \text{ V}$			400	nA
$\begin{array}{c} t_{d(on)} \\ t_r \\ t_d(off) \\ t_f \\ E_{on} \\ E_{off} \end{array}$	$\left\{ \begin{array}{l} \text{Inductive load, } T_{vJ} = 125^{\circ}\text{C} \\ V_{CE} = 300 \text{ V; } I_{C} = 80 \text{ A} \\ V_{GE} = 15/0 \text{ V; } R_{G} = 2.2 \Omega \end{array} \right.$		25 11 150 30 0.8 2.3		ns ns ns mJ mJ
C _{ies}	$V_{_{CE}} = 25 \text{ V}; V_{_{GE}} = 0 \text{V}; \text{f} = 1 \text{MHz}$		4.2		nF
R _{thJC} R _{thJH}	(per IGBT) with heatsink compound (0.42 K/m.K; 50 $\mu\text{m})$		0.66	0.33	K/W K/W

IXYS reserves the right to change limits, test conditions and dimensions.

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C25	= 121 A
V _{CES}	= 600 V
V _{CE(sat) typ.}	= 2.3 V



Pin arangement see outlines

Features

- NPT IGBT's
- positive temperature coefficient of saturation voltage
- fast switching
- FRED diodes
 - fast reverse recovery - low forward voltage
- Industry Standard Package - solderable pins for PCB mounting
- isolated DCB ceramic base plate

Advantages

- space and weight savings
- reduced protection circuits
- leads with expansion bend for stress relief

Typical Applications

- AC and DC motor control
- AC servo and robot drives
- power supplies
- welding inverters

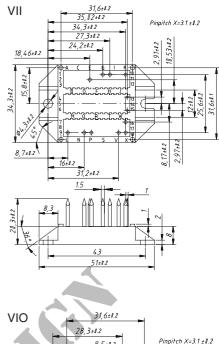
Recommended replacement: Please contact your local sales office

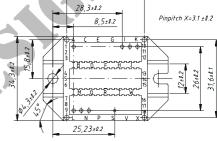
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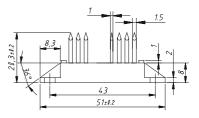


VDI 130-06P1 VII 130-06P1 VID 130-06P1 VIO 130-06P1

Reverse o	liodes (FRED)					
Symbol	Conditions		Maximum Ratings			
I _{F25} I _{F80}	$T_{\rm C} = 25^{\circ}{\rm C}$ $T_{\rm C} = 80^{\circ}{\rm C}$		134. 82.		A A	
Symbol	Conditions	Ch min.	aracteri typ.	istic Va max.		
V _F	$I_{F} = 80 \text{ A}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		1.85 1.40	2.06	V	
I _{RM} t _{rr}	$\left. \begin{array}{l} I_{_{F}} = 60 \text{ A}; di_{_{F}}/dt = 500 \text{ A}/\mu s; T_{_{VJ}} = 125^{\circ}\text{C} \\ V_{_{R}} = 300 \text{ V}; V_{_{GE}} = 0 \text{ V} \end{array} \right.$		28 100		A ns	
R _{thJC} R _{thJH}	with heatsink compound (0.42 K/m.K; 50 µm)		1.32	0.66	K/W K/W	
Temperatu	ure Sensor NTC					
Symbol	Conditions	Chara min.	Characteristic Values min. typ. max.			
R ₂₅ B _{25/50}	T = 25°C	4.75	5.0 3375	5.25	kΩ K	
Module						
Symbol	Conditions Ma	ximum	Rating	ļs		
T VJ T _{stg}			40+15 40+15		°C °C	
V _{ISOL}	$I_{\rm ISOL} \leq 1$ mA; 50/60 Hz		300	00	٧~	
M _d	mounting torque (M4)		1.5 - 2 14 - 1		Nm Ib.in.	
а	Max. allowable acceleration		5	50	m/s²	
Symbol	Conditions		racteris typ.	tic Val max.	ues	
d _s d _A	Creepage distance on surface (Pin to heatsink) Strike distance in air (Pin to heatsink)	11.2 11.2			mm mm	
			0.4	1		







31,6±8.2

Pinpitch X=3.1±0.2

2,58±1.2 7±1.2

28,1±8.2

20,9±0.2

22,35±1.2

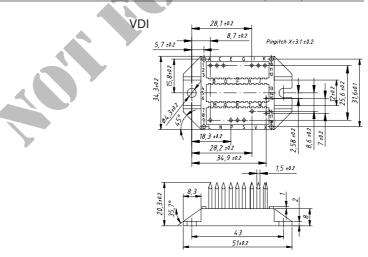
34,9±1.2

1.5

43 51±∎.2

MAAAA

8,7±1.2



24

g

VID

34,3±1.2 . 15.8±1.2

Data according to IEC 60747 and refer to a single transistor or diode unless otherwise stated. IXYS reserves the right to change limits, test conditions and dimensions.

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Weight

14+1